

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

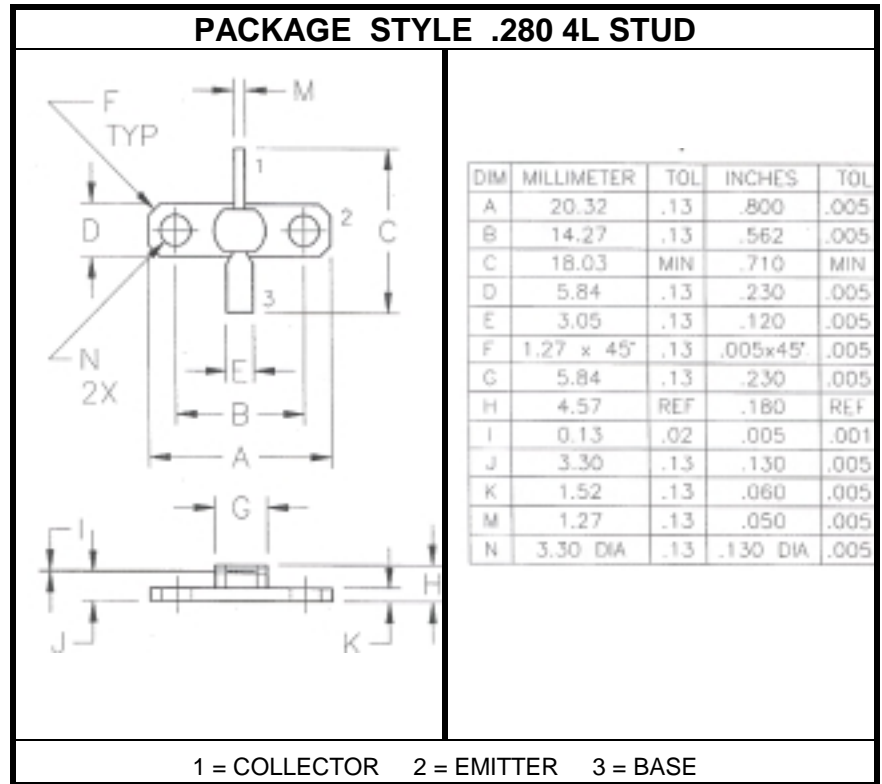
The **ASI TRW54601** is Designed for General Purpose Oscillator Applications up to 2.3 GHz.

**FEATURES:**

- Diffused Ballast Resistors
- **Omnigold™** Metalization System
- Common Emitter

**MAXIMUM RATINGS**

$I_C$	400 mA
$V_{CES}$	50 V
$P_{DISS}$	3.0 W @ $T_C = 25\text{ }^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	35 °C/W


**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 10\text{ mA}$	22			V
$BV_{CES}$	$I_C = 10\text{ mA}$	50			V
$BV_{EBO}$	$I_E = 1.0\text{ mA}$	3.5			V
$I_{CBO}$	$V_{CB} = 28\text{ V}$			0.5	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	20			---
$C_{OB}$	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		2.4	3.0	pF
$P_G$	$V_{CE} = 20\text{ V}$ $I_C = 120\text{ mA}$ $f = 2.3\text{ GHz}$	8.5	9.5		dB
$VSRW$	$P_{OUT} = 0.5\text{ W}$			30:0	---